

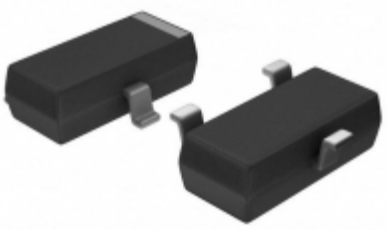


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|  | <p>SI2302DDS-T1-GE3</p> |
| | <p>Hersteller-Teilenummer: SI2302DDS-T1-GE3</p> <p>Hersteller / Marke: Vishay / Siliconix</p> <p>Teil der Beschreibung: MOSFET N-CHAN 20V SOT23</p> <p>Datenblätter:  SI2302DDS-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 24060 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p> |
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| <p>Image may be representation. See specs for product details.</p> | |

Spezifikationen

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|--|---|
| Teilenummer | SI2302DDS-T1-GE3 |
| Hersteller | Vishay / Siliconix |
| Beschreibung | MOSFET N-CHAN 20V SOT23 |
| Kategorie | Diskrete Halbleiterprodukte > Transistoren-FETs, |
| Teilstatus | 24060 pcs Stock |
| Serie | TrenchFET® |
| Technologie | MOSFET (Metal Oxide) |
| Betriebstemperatur | -55°C ~ 150°C (TJ) |
| Befestigungsart | Surface Mount |
| Verpackung / Gehäuse | TO-236-3, SC-59, SOT-23-3 |
| Supplier Device-Gehäuse | SOT-23-3 (TO-236) |
| Verlustleistung (max) | 710mW (Ta) |
| Typ FET | N-Channel |
| FET-Merkmal | - |
| Drain-Source-Spannung (Vdss) | 20V |
| Strom - Ununterbrochener Abfluss (Id) bei 25 ° C | 2.9A (Tj) |
| Rds On (Max) @ Id, Vgs | 57 mOhm @ 3.6A, 4.5V |
| VGS (th) (Max) @ Id | 850mV @ 250µA |
| Gate Charge (Qg) (Max) @ Vgs | 5.5nC @ 4.5V |
| Eingabekapazität (Ciss) (Max) @ Vds | - |
| Antriebsspannung (Max Rds On, Min Rds On) | 2.5V, 4.5V |
| Vgs (Max) | ±8V |
| Verpackung | Tape & Reel (TR) |


SI2302DDS-T1-GE3 ist neu im Original, Suche SI2302DDS-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI2302DDS-T1-GE3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI2302DDS-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

| | | | |
|---|--|--|---|
|  SI2302DC-T1 SILICON SILICON SOT23 |  SI2302DS,215 NXP Semiconductors / Freescale MOSFET N-CH 20V 2.5A SOT23 |  SI2302DS-ES VISHAY SI2302DS-ES VISHAY |  SI2302DS VISHAY SI2302DS VISHAY |
|  SI2302CDS-T1-GE3. VISHAY VISHAY SOT23-5 |  SI2302CDS-T1-GE3 Vishay / Siliconix MOSFET N-CH 20V 2.6A SOT23-3 |  SI2302DS A2SHB VISHAY VISHAY SOT-23 |  SI2302DDS-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CHAN 20V SOT23 |

heiße Teile

Mehr

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|  SI2301BDS-T1-GE3 |  SI2301BDS-T1-GE3 |  SI2301CDS |  SI2301CDS-T1-E3 |  SI2301CDS-T1-E3 |
|  SI2301CDS-T1-GE3 |  SI2301CDS-T1-GE3 |  SI2301DS |  SI2301DS-E3 |  SI2301DS-T1 |
|  SI2301DS-T1-E3 |  SI2301DS-T1-GE3 |  SI2302ADS |  SI2302ADS-T1 |  SI2302ADS-T1 |
|  SI2302ADS-T1-E3 |  SI2302ADS-T1-E3 |  SI2302ADS-T1-GE3 |  SI2302ADS-T1-GE3 |  SI2302BDS-T1-E3 |
|  SI2302CDS-T1-E3 |  SI2302CDS-T1-E3 |  SI2302CDS-T1-GE3 |  SI2302CDS-T1-GE3 |  SI2302DDS-T1-GE3 |
|  SI2302DS |  SI2302DS-ES |  SI2302DS-T1 |  SI2302DS-T1-E3 |  SI2302DS-T1-GE3 |
|  SI2302DV |  SI2302WCB |  SI2303ADS-T1-GE3 |  SI2303BDS |  SI2303BDS-T |
|  SI2303BDS-T1 |  SI2303BDS-T1 |  SI2303BDS-T1-E3 |  SI2303BDS-T1-E3 |  SI2303BDS-T1-GE3 |
|  SI2303BDS-T1-GE3 |  SI2303BDS/A5 |  SI2303CDS |  SI2303CDS-T1-E3 |  SI2303CDS-T1-E3 |
|  SI2303CDS-T1-GE3 |  SI2303CDS-T1-GE3 |  SI2303DL-T1-E3 |  SI2303DS |  SI2303DS-T1 |

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